

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE													
INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION													
DOCKET NO.: 007352 USA/ETCH/DRIE/JB APPLICATION NO.: 10/615,159													
APPLICANT: Frum et al.													
FILING DATE: 7/7/2003 GROUP ART UNIT: 1763													
U.S. PATENT DOCUMENTS													
EXAMINER INITIAL	DOCUMENT NUMBER							DATE	NAME	CLASS	SUB- CLASS	FILING DATE IF APPROPRIATE	
GAG	5	4	5	0	2	0	5	09/12/1995	Sawin, et al.				
	5	5	0	3	7	0	7	04/02/1996	Maung, et al.				
	5	5	6	4	8	3	0	10/15/1996	Bobel, et al.				
	5	6	5	8	4	1	8	08/19/1997	Coronel, et al.				
	5	7	5	6	4	0	0	05/26/1998	Ye, et al.				
	6	0	8	1	3	3	4	06/27/2000	Grimbergen, et al.				
	6	1	6	5	3	1	1	12/26/2000	Collins, et al.				
	4	1	4	7	4	3	5	04/30/1979	Habegger				
	4	8	4	6	9	2	8	07/11/1989	Dolins, et al.				
GAG	4	8	4	7	7	9	2	07/11/1989	Bama, et al.				
FOREIGN PATENT DOCUMENTS													
	DOCUMENT NUMBER							DATE	COUNTRY	CLASS	SUB- CLASS	TRANSLATION	
												YES	NO
OTHER DOCUMENTS (<i>Including Author, Title, Date, Pertinent Pages, etc.</i>)													
GAG	Maynard, et al., "Multiwavelength Ellipsometry for Real-time Process Control of the Plasma Etching of Patterned Samples." J. Vac Sci Technol. B. 15 (1), Jan/Feb 1997, pages 109-115 ✓												
GAG	Klemens, F.P., et al., "High Density Plasma Gate Etching of 0.12 µm Devices with Sub 1.5 nm Gate-Oxides." Electrochemical Society Proceedings. Volume 97-30, pages 85-95												
EXAMINER	George Goudreau										DATE CONSIDERED 5-041		
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.													